

## The Ideal Diode

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## Background

- There exist some signal processing functions that can be only implemented by nonlinear circuit
  - generation of dc voltages from the ac power supply
  - signal generations (e.g., square waves, sinusoids waves)
  - digital logic
  - memory circuits
- A diode is a fundamental nonlinear circuit element.

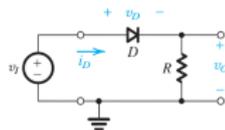


FIG 1. A diode rectifier

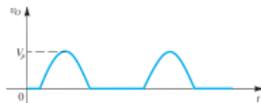
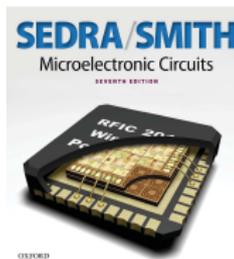


FIG 2. output of the rectifier

## Readings

- Read section 4.1 on pages 175- 184
- Do and understand example 4.2 on page 181
- Do exercises 4.1, 4.2 and 4.3 on page 179
- Do exercises 4.4 and 4.5 and 4.3 on page 183



- 1 Readings are based on Sedra & Smith (2014), Microelectronic Circuits 7th edition.
- 2 Bold reading sections are mandatory. Other sections are suggested but not required readings

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## What is a diode

- Diodes are essentially one-way current gates
- Diodes are made of semiconductors —usually silicon—that consist of stack of p-doped and n-doped silicon to form a p-n junction
- A diode has two terminals and typically allows the flow of current in one direction only.

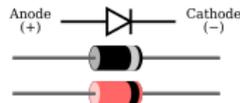


FIG 3. Typical diode packages in same alignment as diode symbol. Thin bar depicts the cathode<sup>1</sup>

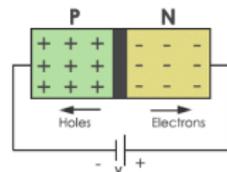


FIG 4. n-types and p-type arrangement in a diode

# What is a diode?

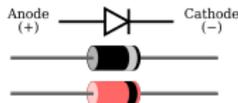


FIG 5. Typical diode packages in same alignment as diode symbol. Thin bar depicts the cathode<sup>1</sup>

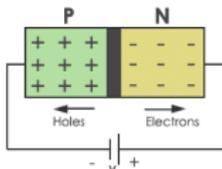


FIG 6. n-types and p-type arrangement in a diode

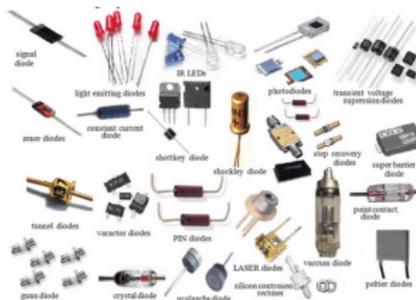


FIG 7. Various types of diodes<sup>1</sup>

<sup>1</sup>Gupta, K. M., & Gupta, N. (2015). Different Types of Diodes, Ideal and Real Diodes, Switching Diodes, Abrupt and Graded Junctions. Engineering Materials, 235–259

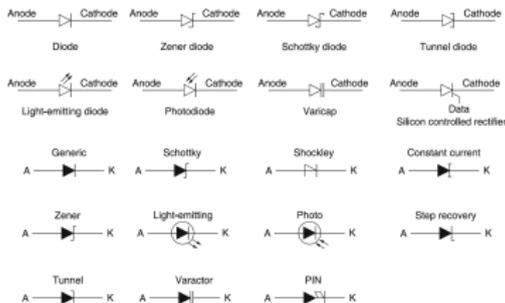


FIG 8. Various types of diodes and their schematic symbols<sup>2</sup>

## Characteristics of Ideal Diode

- An ideal diode would be a perfect diode without any flaws (Fig. 9)
- Characteristics of ideal diode when forward biased
  - Zero resistance
  - Infinite amount of current
  - Zero threshold voltage,  $V_T$
- Characteristics of an ideal diode when reverse biased
  - Infinite resistance
  - Zero reverse leakage current
  - No reverse breakdown

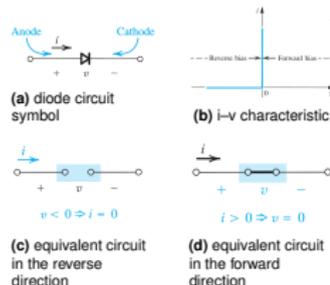


FIG 9. The ideal diode

<sup>2</sup>Gupta, K. M., & Gupta, N. (2015). Different Types of Diodes, Ideal and Real Diodes, Switching Diodes, Abrupt and Graded Junctions. Engineering Materials, 235–259

# Real diode

Real diodes do not follow the ideal diode equation because of physical limitations of device fabrication or design techniques. In a real diode:

- $R_F$  is of the order of a few ohms.
- $V_F \approx 0.7$  for silicon and  $V_F \approx 0.3$  for germanium based diodes.
- Reverse bias resistance  $R_r$  is of the order of a few kilo ohms.

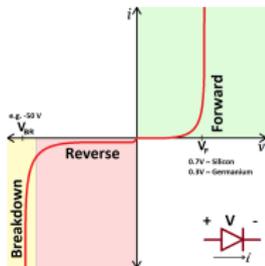


FIG 10. The I-V relationship of a real diode<sup>2</sup>

TAB 1. Ideal diode versus real diode

Ideal diode	Real diode
No reverse leakage current	There exists some leakage current
Can behave as a perfect conductor ( $R=0$ )	No such perfection exists in the real-world
Can behave as a perfect insulator ( $R = \infty$ )	No such perfection exists in the real-world
Draws no current when reverse biased	Normally draws very low current in reverse bias
Have infinite resistance	Have high resistance, but not infinite
No voltage drops when forward biased.	very low voltage drop when forward biased.
Acts like a short circuit in the forward-bias mode	$V_F \neq 0$ when current flows through it
Acts like an open circuit in a reverse-bias mode	Reverse-bias resistance is of a few kilo-ohms
It cannot be manufactured.	it is manufactured, duh!

<sup>2</sup><https://learn.sparkfun.com/tutorials/diodes/real-diode-characteristics>

## EXAMPLE—1N4148 diode characteristics

ELECTRICAL CHARACTERISTICS ( $T_{amb} = 25^\circ C$ , unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 10 \text{ mA}$	$V_F$			1	V
	$V_F = 20 \text{ V}$	$I_{FR}$			25	nA
Reverse current	$V_{RR} = 20 \text{ V}, T_J = 150^\circ C$	$I_{RR}$			50	$\mu A$
	$V_{RR} = 75 \text{ V}$	$I_{RR}$			5	$\mu A$
Breakdown voltage	$I_{BR} = 100 \mu A, I_F/T = 0.01, V_{RR} = 0.3 \text{ ms}$	$V_{BR}$	100			V
Diode capacitance	$V_{RR} = 0 \text{ V}, f = 1 \text{ MHz}, V_{RR} = 50 \text{ mV}$	$C_D$			4	pF
Rectification efficiency	$V_{RR} = 2 \text{ V}, f = 100 \text{ MHz}$	$\eta_r$		45		%
Reverse recovery time	$I_F = I_{FR} = 10 \text{ mA}, I_{RR} = 1 \text{ mA}$	$t_{rr}$			8	ns
	$I_F = 10 \text{ mA}, V_{RR} = 6 \text{ V}, I_{RR} = 0.1 \times I_{FR}, R_L = 100 \Omega$	$t_{rr}$			4	ns

FIG 11. Electrical characteristics of a 1N4148 diode

The 1N4148 diode is a standard silicon switching signal diode. The 1N4148 was first developed 1960 by Texas Instruments and is useful in switching applications up to about 100 MHz with a reverse-recovery time of no more than 4ns

## EXAMPLE—1N4148 diode characteristics

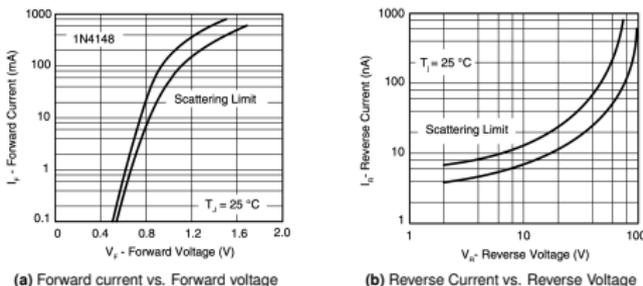


FIG 12. Typical behaviors of 1N4148 diode at  $T = 25^\circ C$

<sup>2</sup>The 1N4148's datasheet is available at

## Application—the rectifier circuit

- **Rectifier**—A circuit which converts AC waves in to DC.
- The diode blocks reverse current flow, preventing negative voltage across the resistor  $R$ .

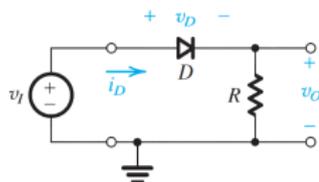
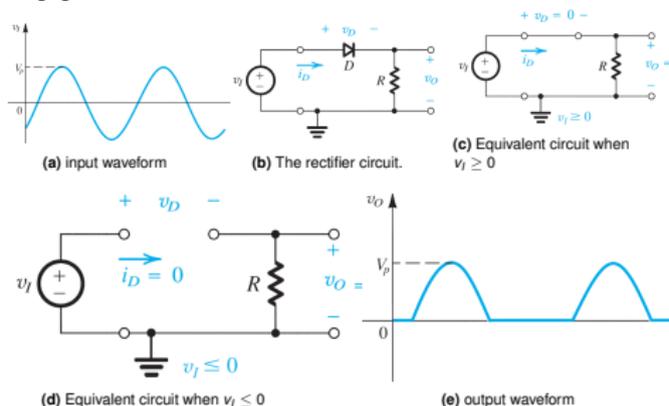


FIG 13. A rectifier circuit

## Application—the rectifier circuit



## Application—diode logic gates

- **OR logic gate (Fig. 15a)**
  - If  $v_A = 5V$ , then the diode  $D_A$  will conduct and  $v_Y = v_A = 5V$
  - Similarly, if any diode conducts, then  $v_Y = 5V$
  - The output  $v_Y = v_A + v_B + v_C$
- **AND gate (Fig. 15b)**
  - If  $v_A = 0V$  then diode  $D_A$  will conduct and  $v_Y = v_A = 0V$
  - If all diodes block then  $v_Y = 5V$
  - The output

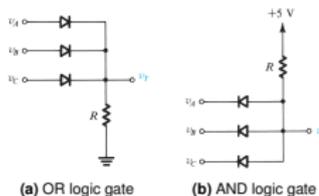


FIG 15. Diode logic gates

The end